

Kwan-Yong Lim

List of Publications by Year in descending order

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citing authors

#	ARTICLE	IF	CITATIONS
1	Gate Oxide Reliability Characterization of Tungsten Polymetal Gate with Low-Contact-Resistive WSi _x /WN Diffusion Barrier in Memory Devices. Japanese Journal of Applied Physics, 2007, 46, 7256.	1.5	5
2	Studies on the interfacial and crystallographic characteristics of Al ₂ O ₃ •SiO ₂ •Si and ZrO ₂ •SiO ₂ •Si stacks. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2005, 23, 144.	1.6	4
3	Suppressed boron penetration in p+ polycrystalline-Si/Al ₂ O ₃ /Si metal-oxide-semiconductor structures. Applied Physics Letters, 2002, 80, 3177-3179.	3.3	10
4	Impact of atomic-layer-deposited TiN on the gate oxide quality of W/TiN/SiO ₂ /Si metal-oxide-semiconductor structures. Applied Physics Letters, 2002, 80, 2514-2516.	3.3	47
5	Electrical characteristics and thermal stability of n ⁺ polycrystalline- Si/ZrO ₂ /SiO ₂ /Si metal-oxide-semiconductor capacitors. Journal of Applied Physics, 2002, 91, 414.	2.5	40
6	Boron penetration and thermal instability of p ⁺ polycrystalline-Si/ZrO ₂ /SiO ₂ /n-Si metal-oxide-semiconductor structures. Journal of Applied Physics, 2002, 91, 65.	2.5	13
7	Effects of TiN Deposition on the Characteristics of W/TiN/SiO ₂ /Si Metal Oxide Semiconductor Capacitors. Journal of the Electrochemical Society, 2001, 148, F189.	2.9	14
8	Characteristics of n+ polycrystalline-Si/Al ₂ O ₃ /Si metal-oxide-semiconductor structures prepared by atomic layer chemical vapor deposition using Al(CH ₃) ₃ and H ₂ O vapor. Journal of Applied Physics, 2001, 89, 6275-6280.	2.5	80
9	XPS core-level shifts and XANES studies of Cu-Pt and Co-Pt alloys. Surface and Interface Analysis, 2000, 30, 475-478.	1.8	46